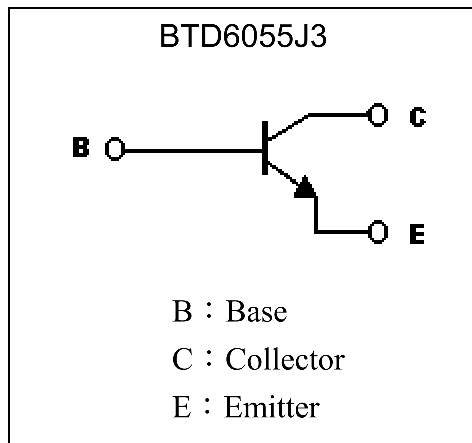
Low Vcesat NPN Epitaxial Planar Transistor

BTD6055J3

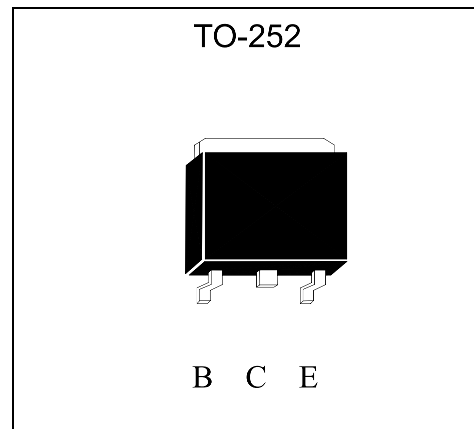
Features

- Low $V_{CE(SAT)}$
- Low $R_{CE(SAT)}$, $R_{CE(SAT)}$=50 mΩ (typically) at I_C=5A
- Low operating collector voltage
- Excellent current gain characteristics at very low V_{CE}
- Suitable for low dropout voltage application
- Pb-free package

Symbol



Outline



Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V_{CBO}	15	V
Collector-Emitter Voltage	V_{CEO}	10	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector Current (DC)	I_C	6	A
Collector Current (Pulse)	I_{CP}	9 (Note 1)	
Power Dissipation @ T_A=25℃	P_D	1 (Note 2)	W
Power Dissipation @ T_C=25℃	P_D	15	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	71.4 (Note 2)	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	6.25	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~+150	°C

Note : 1. Single Pulse , Pw≦380μs,Duty≦2%.
2. When mounted on a PCB with the minimum pad size.

Characteristics (Ta=25°C)

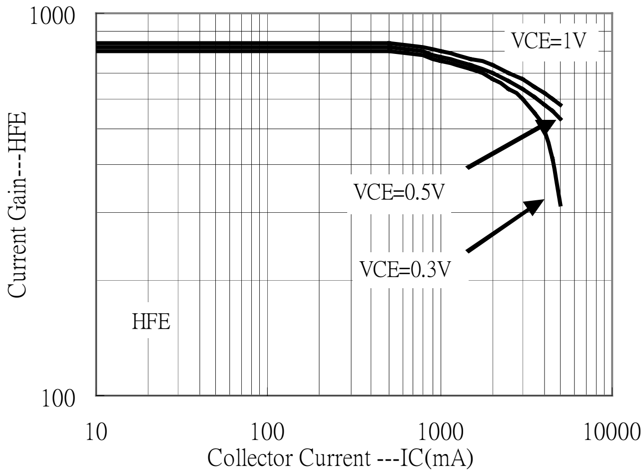
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CEO}	10	-	-	V	I_C=1mA, I_B=0
I_{CBO}	-	-	100	nA	V_{CB}=12V, I_E=0
I_{EBO}	-	-	100	nA	V_{EB}=7V, I_C=0
*$V_{CE(sat)}$	-	-	0.2	V	I_C=3A, I_B=20mA
*$V_{CE(sat)}$	-	-	0.35	V	I_C=5A, I_B=20mA
*$V_{BE(sat)}$	-	-	1.2	V	I_C=3A, I_B=60mA
*$V_{BE(on)}$	-	-	1.2	V	V_{CE}=0.3V, I_C=3A
*h_{FE}	450	-	-	-	V_{CE}=0.3V, I_C=500mA
*h_{FE}	400	-	-	-	V_{CE}=0.3V, I_C=1A
*h_{FE}	250	-	-	-	V_{CE}=0.3V, I_C=5A
f_T	100	-	-	MHz	V_{CE}=6V, I_C=500mA, f=20MHz
Cob	-	-	50	pF	V_{CB}=10V, f=1MHz

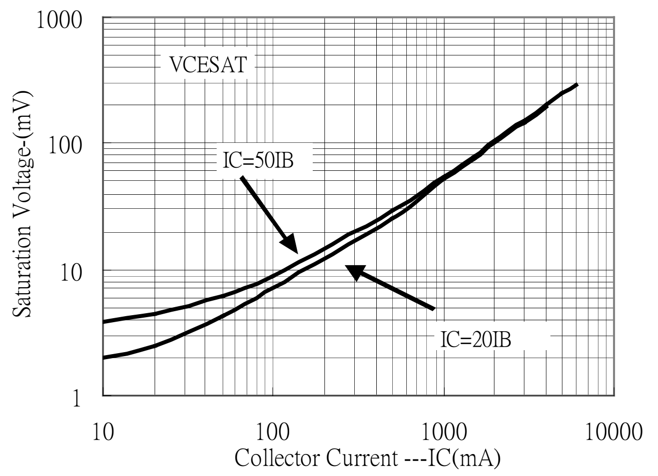
*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

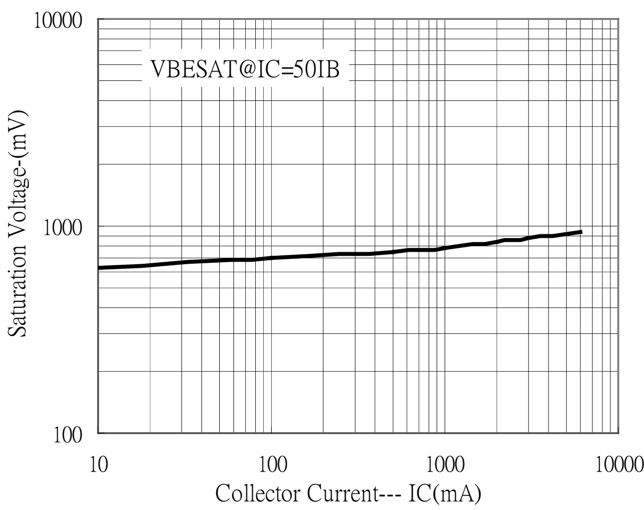
Ordering Information

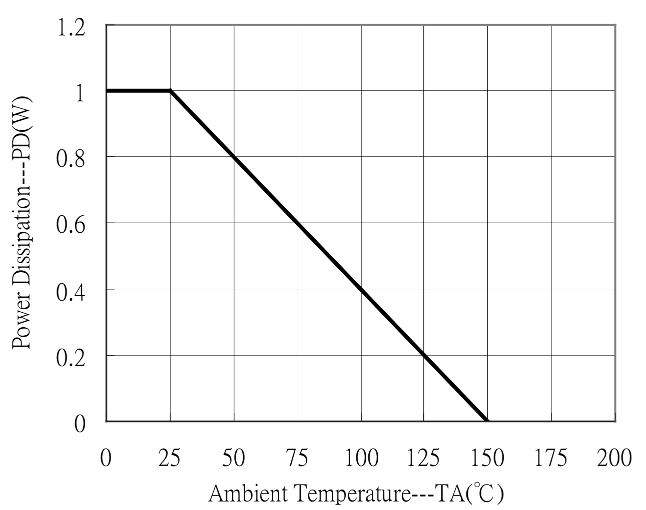
Device	Package	Shipping	Marking
BTD6055J3	TO-252 (Pb-free)	2500 pcs / Tape & Reel	D6055

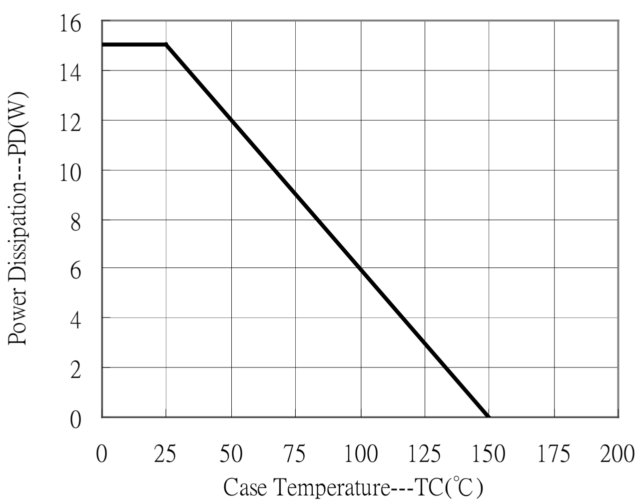
Characteristic Curves



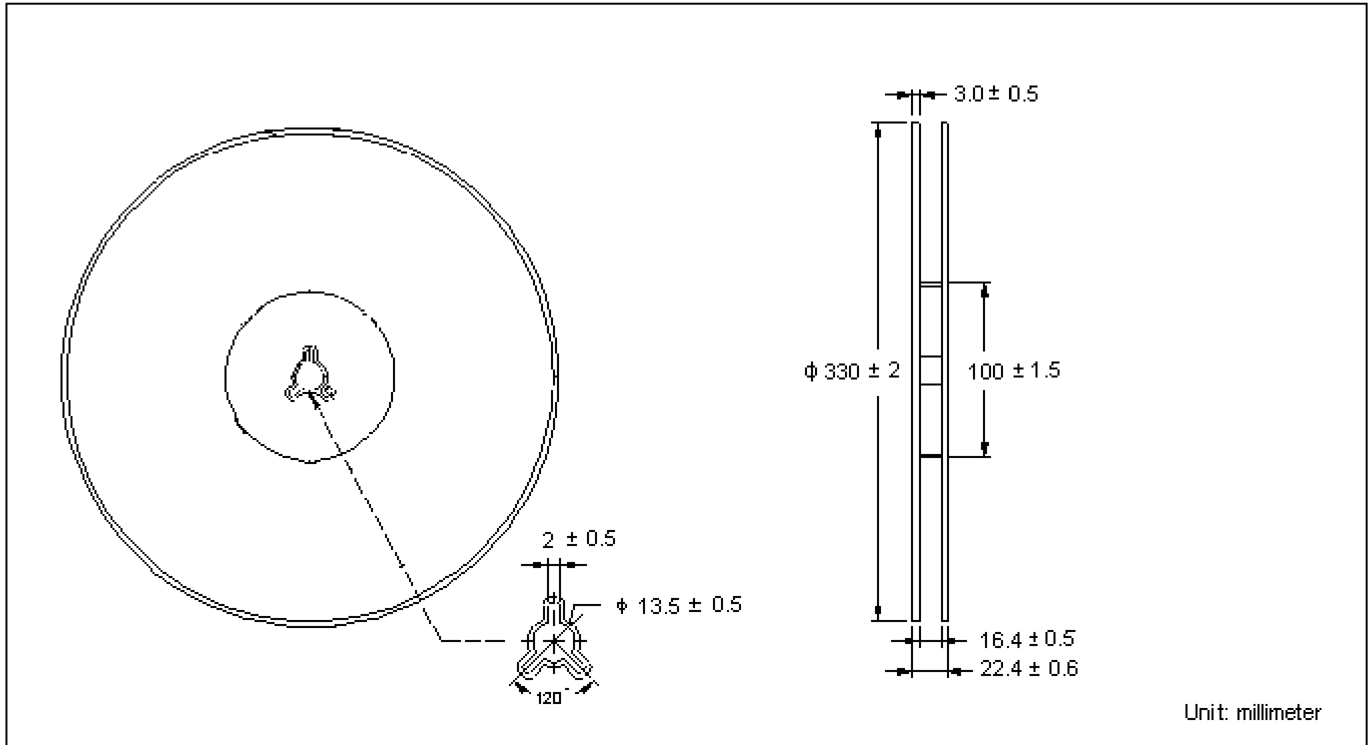




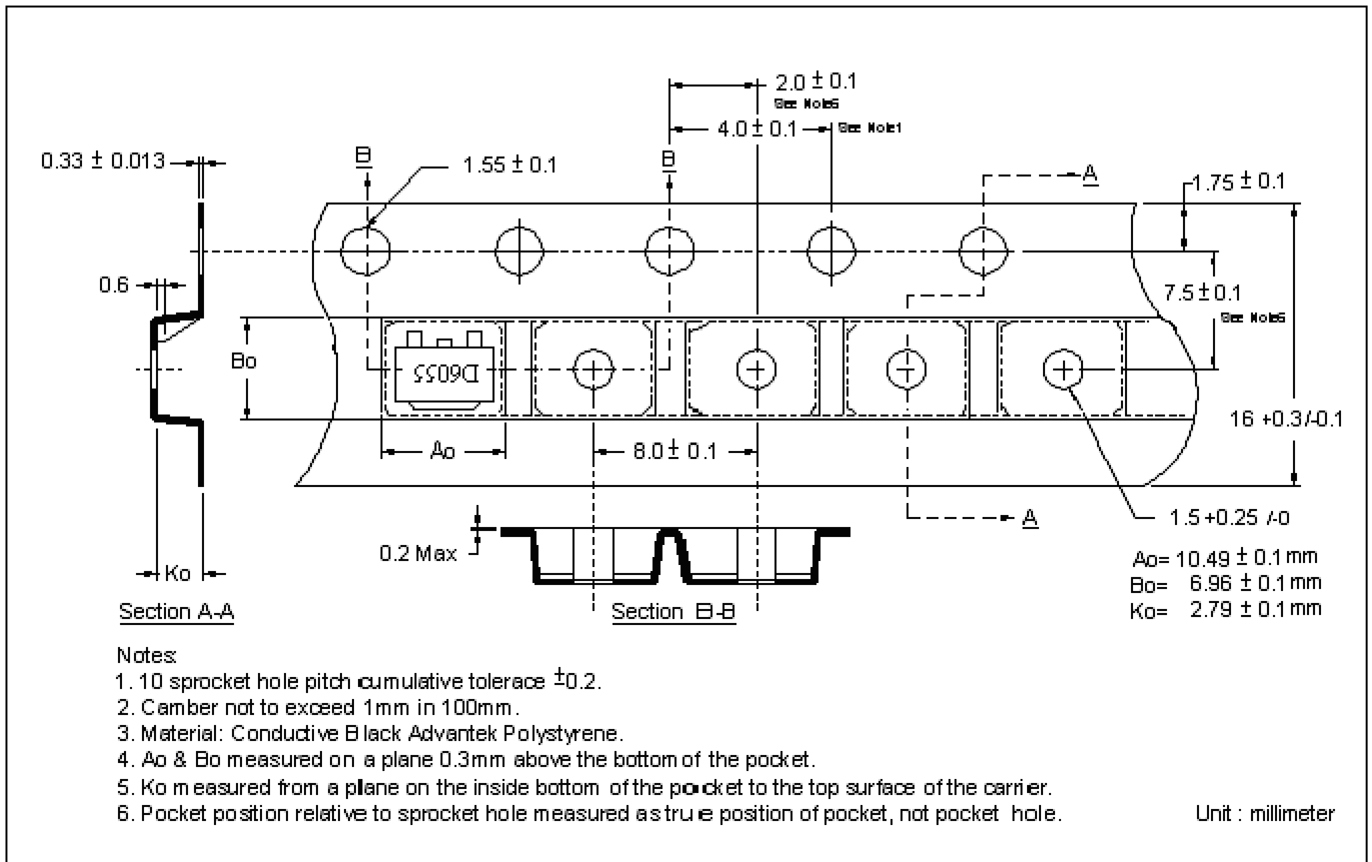




Reel Dimension



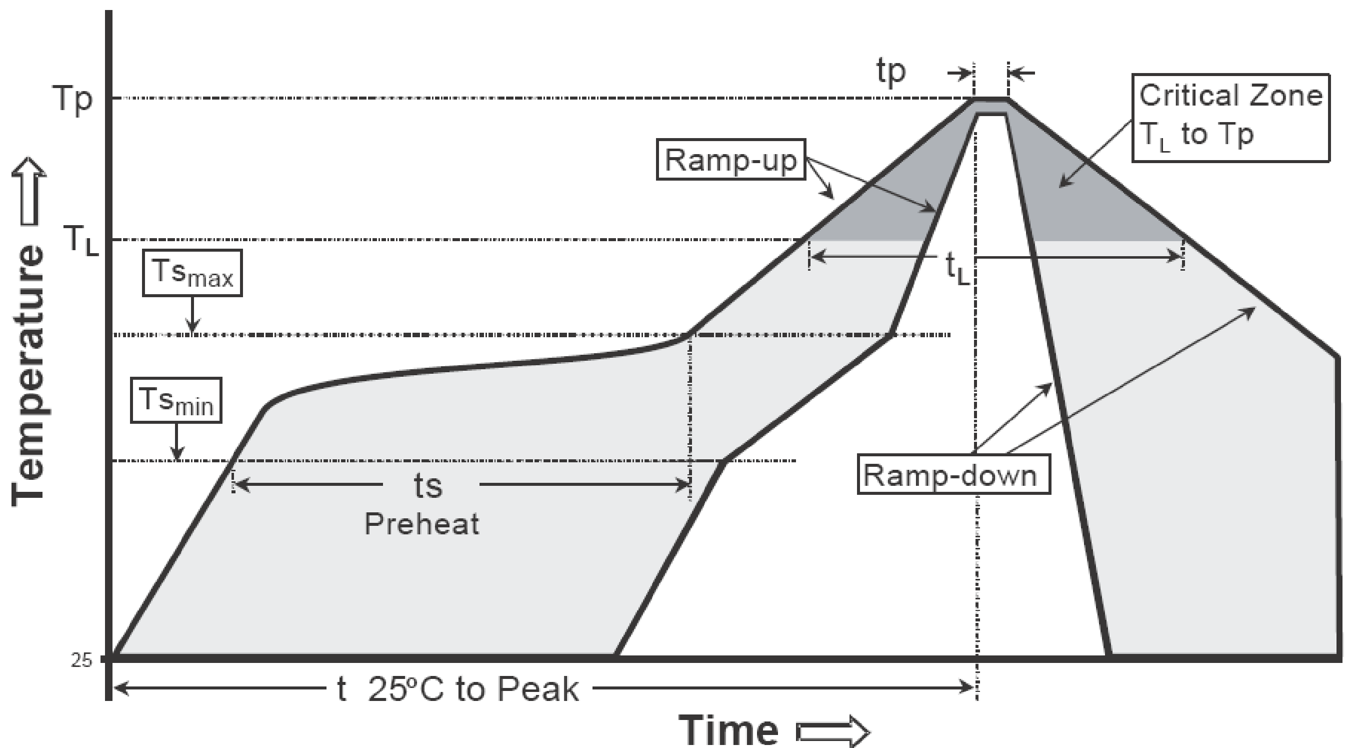
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

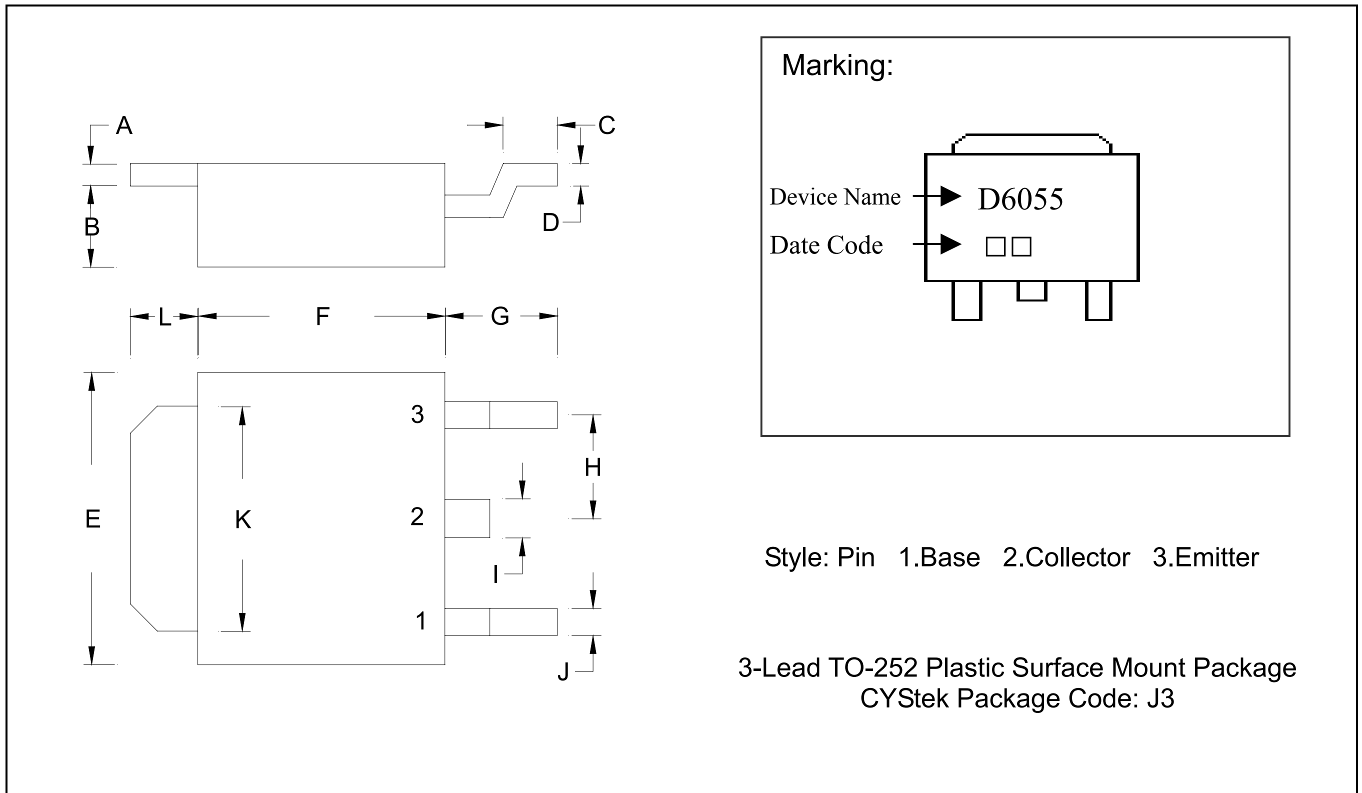
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat −Temperature Min(T_S min) −Temperature Max(T_S max) −Time(ts_{min} to ts_{max})	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: −Temperature (T_L) − Time (t_L)	183°C 60-150 seconds	217°C 60-150 seconds
Peak Temperature(T_P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-252 Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0177	0.0217	0.45	0.55	G	0.0866	0.1102	2.20	2.80
B	0.0650	0.0768	1.65	1.95	H	-	*0.0906	-	*2.30
C	0.0354	0.0591	0.90	1.50	I	-	0.0354	-	0.90
D	0.0177	0.0236	0.45	0.60	J	-	0.0315	-	0.80
E	0.2520	0.2677	6.40	6.80	K	0.2047	0.2165	5.20	5.50
F	0.2125	0.2283	5.40	5.80	L	0.0551	0.0630	1.40	1.60

Notes: 1.Controlling dimension: millimeters.
2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: KFC; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of CYStek.
- CYStek reserves the right to make changes to its products without notice.
- CYStek ***semiconductor products are not warranted to be suitable for use in Life-Support Applications, or systems.***
- CYStek assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.